

isc Silicon NPN Power Transistor

2SD900

DESCRIPTION

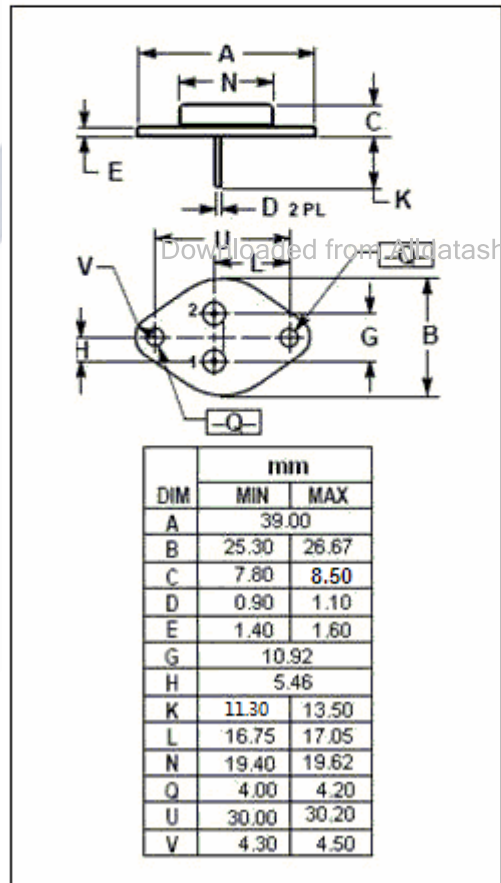
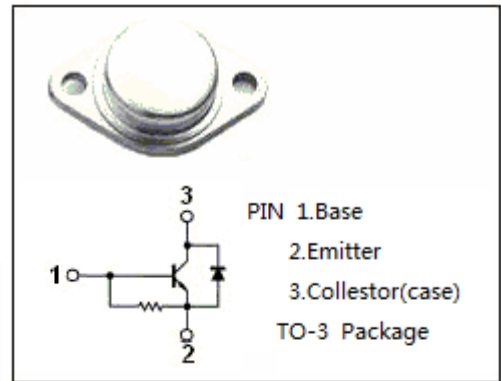
- High Breakdown Voltage-
: $V_{CBO} = 1500V$ (Min)
- High Switching Speed
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 5.0V$ (Max.) @ $I_C = 4.5A$
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in color TV deflection circuits.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector- Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	5	A
I_{CM}	Collector Current- Peak	6	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	50	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-45~150	$^\circ C$



isc Silicon NPN Power Transistor**2SD900****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{EBO}	Emitter-Base Breakdown Voltage	$I_E= 300\text{mA}; I_C= 0$	6.0			V
I_{CES}	Collector Cutoff Current	$V_{CE}= 1500\text{V}; V_{BE}= 0$			0.5	mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 4.5\text{A}; I_B= 1.2\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 4.5\text{A}; I_B= 1.2\text{A}$			1.5	V
h_{FE}	DC Current Gain	$I_C= 1\text{A}; V_{CE}= 5\text{V}$	10		40	
V_{ECF}	C-E Diode Forward Voltage	$I_F= 6\text{A}$			3.0	V
t_f	Fall Time	$I_C=4\text{A}, I_{B1}= 1.1\text{A}, I_{B2}= 1.6\text{A}$			1.0	μs

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